

S202SE1/S202SE2 S216SE1/S216SE2

SIP Type SSR for Medium Power Control

■ Features

- Comforms to European Safety Standard (EN60950)
(Need of the insulation sheet when mounting external heat sink)
Internal insulation distance : 0.4mm or more
Creepage distance : 5mm or more
Space distance : 4mm or more
- RMS ON-state current
S202SE1 / S202SE2 : 8Arms at $T_c \leq 80^\circ\text{C}$
(with heat sink)
S216SE1 / S216SE2 : 16Arms at $T_c \leq 60^\circ\text{C}$
(with heat sink)
- Isolation voltage between input and output (V_{iso} : 3 000V_{rms})
- Approved by TÜV, No. R9051479
- Recognized by UL, No. E94758
(S202SE1 / S202SE2)
Approved by CSA, No. LR63705
(S202SE1, S202SE2)

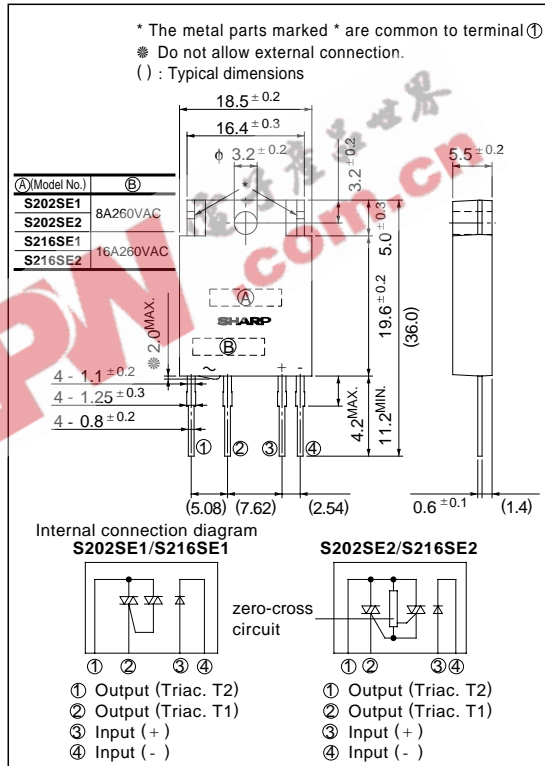
■ Applications

- Copiers
- Laser beam printers

■ Line-up

	RMS ON-state current	
	MAX. 8Arms	MAX. 16Arms
No built-in Zero-cross circuit	S202SE1	S216SE1
Built-in Zero-cross circuit	S202SE2	S216SE2

■ Outline Dimensions (Unit : mm)



■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating		Unit
		S202SE1/S202SE2	S216SE1/S216SE2	
Input	Forward current	I _F 50		mA
	Reverse voltage	V _R 6		V
Output	RMS ON-state current	I _T *4	*516	A _{rms}
	*1 Peak one cycle surge current	I _{surge} 80	160	A
	Repetitive peak OFF-state voltage	V _{DRM} 600		V
	Non-repetitive peak OFF-state voltage	V _{DSM} 600		V
	Critical rate of rise of ON-state current	dI _T /dt 50		A/μs
	Operating frequency	f 45 to 65		Hz
*2 Isolation voltage	V _{iso} 3,000		V _{rms}	
Operating temperature	T _{opr} - 25 to + 100		°C	
Storage temperature	T _{stg} - 30 to + 125		°C	
*3 Soldering temperature	T _{sol} 260		°C	

*1 60Hz sine wave, T_j = 25°C start

*2 AC 60Hz for 1 minute, 40 to 60% RH. Apply voltages between input and output by the dielectric withstand voltage tester with zero-cross circuit.(Input and output shall be shorted respectively).

(Note) When the isolation voltage is necessary at using external heat sink, please use the insulation sheet.

*3 For 10 seconds *4 T_c ≤ 80°C *5 T_c ≤ 60°C

Electrical Characteristics

(Ta = 25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage	V_F	$I_F = 20\text{mA}$	-	1.2	1.4	V	
	Reverse current	I_R	$V_R = 3\text{V}$	-	-	10^{-4}	A	
Repetitive peak OFF-state current		I_{DRM}	$V_D = V_{DRM}$	-	-	10^{-4}	A	
Output	ON-state voltage	V_T	$I_T = 2A_{rms}$	-	-	1.5	V_{rms}	
			$I_T = 16A_{rms}$	-	-	1.5		
Holding current		I_H	-	-	-	50	mA	
Critical rate of rise of OFF-state voltage		dV/dt	$V_D = 2/3V_{DRM}$	30	-	-	V/ μs	
Critical rate of rise of commutating OFF-state voltage		$(dV/dt)_c$	$T_j = 125^\circ\text{C}, V_D = 400\text{V} *6$	5	-	-	V/ μs	
Zero-cross voltage		S202SE2 / S216SE2 V_{OX}	$I_F = 8\text{mA}$	-	-	35	V	
Transfer characteristics	Minimum trigger current	I_{FT}	S202SE1 / S216SE1 $V_D = 12\text{V}, R_L = 30\Omega$	-	-	8	mA	
			S202SE2 / S216SE2 $V_D = 6\text{V}, R_L = 30\Omega$	-	-	8		
	Isolation resistance		R_{ISO}	DC500V, 40 to 60 % RH	10^{10}	-	-	Ω
	Turn-on time	t_{on}	S202SE1 / S216SE1	AC60Hz	-	-	1	ms
S202SE2 / S216SE2			AC60Hz	-	-	9.3		
Turn-off time		t_{off}	AC60Hz	-	-	9.3	ms	
Thermal resistance (Between junction and case)		$R_{th(j-c)}$	-	-	4.5	-	$^\circ\text{C/W}$	
								S202SE1 / S202SE2
		$R_{th(j-a)}$	-	-	40	-	$^\circ\text{C/W}$	
								S216SE1 / S216SE2

*6 $dI_T/dt = -4.0\text{A/ms}$ (**S202SE1 / S202SE2**)
 $dI_T/dt = -8.0\text{A/ms}$ (**S216SE1 / S216SE2**)

Fig.1-a RMS ON-state Current vs. Ambient Temperature
(S202SE1 / S202SE2)

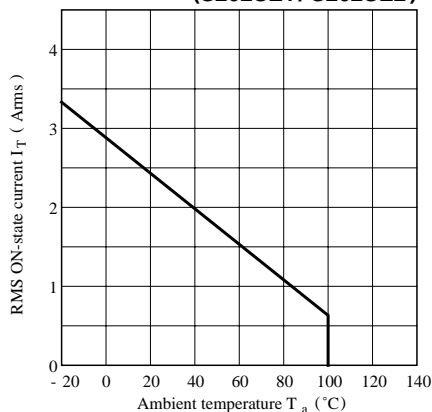


Fig.1-b RMS ON-state Current vs. Ambient Temperature
(S216SE1 / S216SE2)

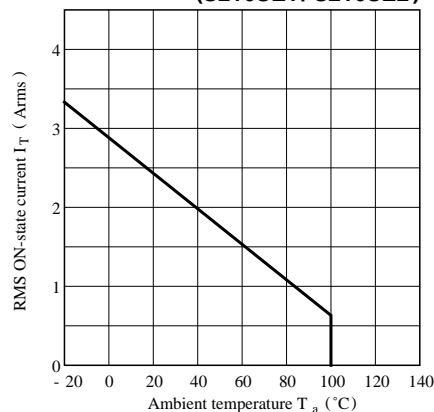


Fig.2-a RMS ON-state Current vs. Case Temperature (S202SE1 / S202SE2)

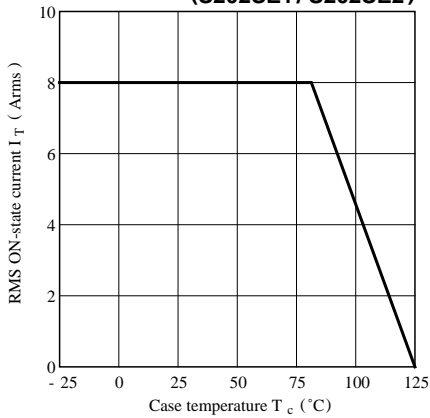


Fig.2-b RMS ON-state Current vs. Case Temperature (S216SE1 / S216SE2)

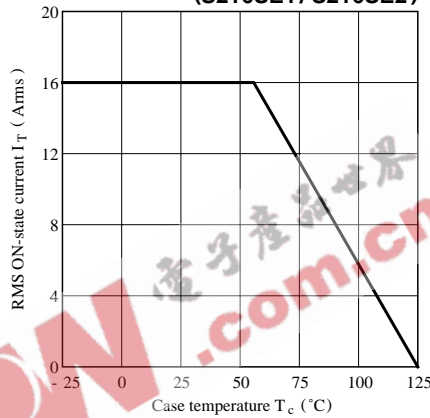


Fig. 3 Forward Current vs. Ambient Temperature

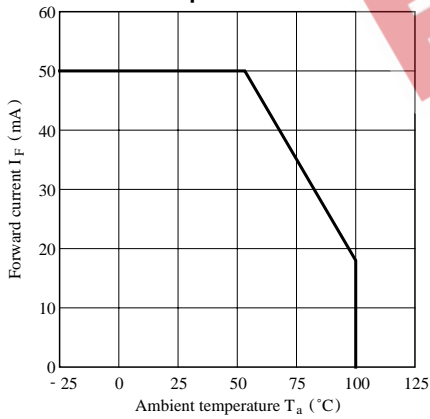


Fig. 4 Forward Current vs. Forward Voltage

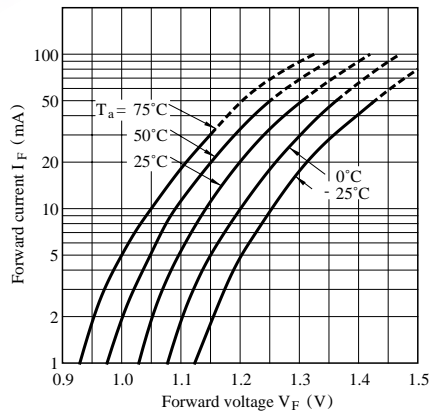


Fig.5-a Surge Current vs. Power-ON Cycle (S202SE1 / S202SE2)

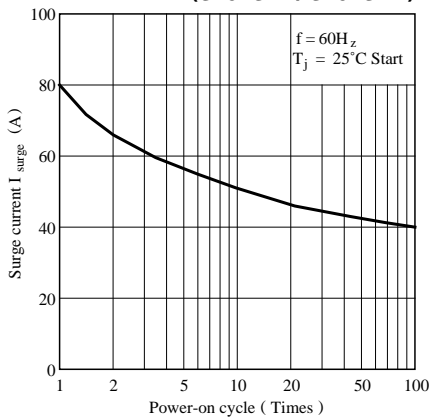


Fig.5-b Surge Current vs. Power-ON Cycle (S216SE1 / S216SE2)

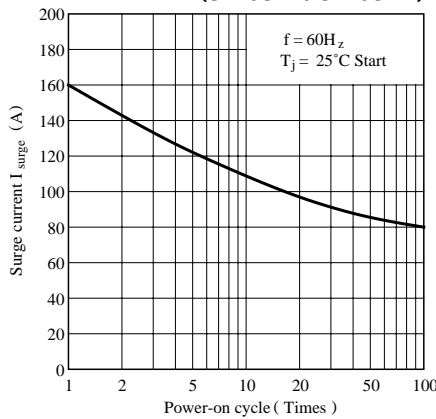


Fig.6-a Maximum ON-State Power Dissipation vs. RMS ON-State Current (S202SE1 / S202SE2)

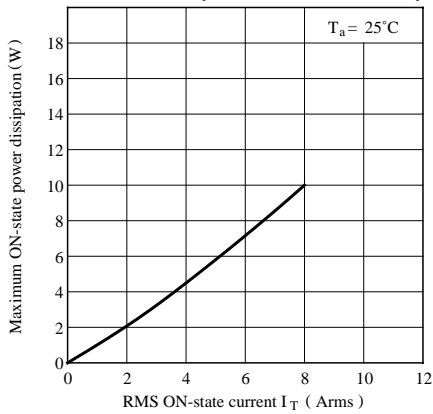


Fig.6-b Maximum ON-State Power Dissipation vs. RMS ON-State Current (S216SE1 / S216SE2)

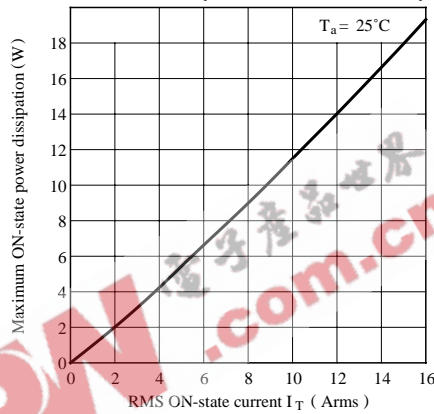


Fig.7-a Minimum Trigger Current vs. Ambient Temperature (Typical Value) (S202SE1 / S216SE1)

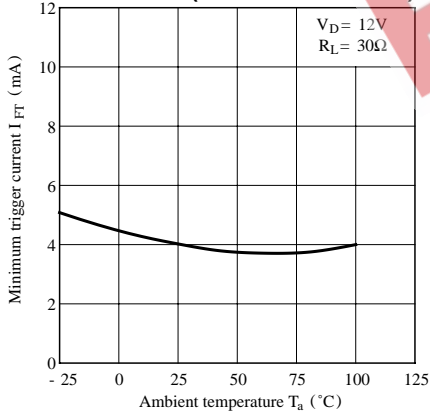


Fig.7-b Minimum Trigger Current vs. Ambient Temperature (Typical Value) (S202SE2 / S216SE2)

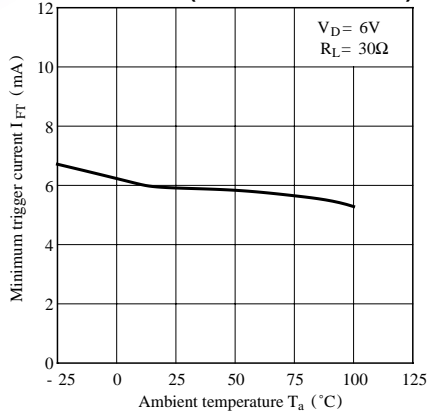


Fig.8-a Repetitive Peak OFF-state Current vs. Ambient Temperature (Typical Value) (S202SE1 / S202SE2)

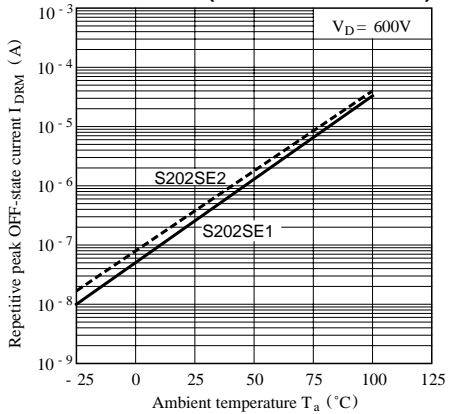


Fig.8-b Repetitive Peak OFF-state Current vs. Ambient Temperature (Typical Value) (S216SE1 / S216SE2)

